

In the Claims:

1 1. (currently amended) A method of processing a surface of a
2 nitride semiconductor crystal, wherein

3 a surface of a nitride semiconductor crystal ~~[(11)]~~
4 is brought into contact with a liquid containing at least
5 Na, Li or Ca as a processing ~~solution (15)~~. solution.

1 2. (currently amended) The method of processing a surface of
2 a nitride semiconductor crystal according to claim 1,
3 wherein

4 said processing solution ~~[(15)]~~ is a liquid
5 containing at least Na and has an Na content of 5-95 mol%.

1 3. (currently amended) The method of processing a surface of a
2 nitride semiconductor crystal according to claim 1, wherein

3 said processing solution ~~[(15)]~~ is a liquid
4 containing at least Li and has an Li content of 5-100 mol%.

1 4. (currently amended) The method of processing a surface of
2 a nitride semiconductor crystal according to claim 1,
3 wherein

4 said nitride semiconductor crystal ~~[(11)]~~ is an
5 $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ semiconductor crystal ($0 \leq x \leq 1$, $0 \leq y \leq 1$,
6 $0 \leq x + y \leq 1$).

5. (currently amended) A nitride semiconductor crystal having a maximum depth of a surface scratch of at most 0.01 μm and obtained with a method of processing a surface of a nitride semiconductor crystal wherein a surface of a nitride semiconductor crystal ~~[[(+11)]]~~ is brought into contact with a liquid containing at least Na, Li or Ca as a processing ~~solution (+15).~~ solution.

6. (currently amended) The nitride semiconductor crystal according to claim 5, wherein said processing solution ~~[[(+15)]]~~ is a liquid containing at least Na and has an Na content of 5-95 mol%.

7. (currently amended) The nitride semiconductor crystal according to claim 5, wherein said processing solution ~~[[(+15)]]~~ is a liquid containing at least Li and has an Li content of 5-100 mol%.

8. (currently amended) The nitride semiconductor crystal according to claim 5, wherein said nitride semiconductor crystal ~~[[(+11)]]~~ is an $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ semiconductor crystal ($0 \leq x \leq 1$, $0 \leq y \leq 1$, $0 \leq x + y \leq 1$).

9. (currently amended) A nitride semiconductor crystal having an average thickness of a damaged layer of at most 2 μm and

3 obtained with a method of processing a surface of a nitride
4 semiconductor crystal wherein a surface of a nitride
5 semiconductor crystal ~~[(11)]~~ is brought into contact with
6 a liquid containing at least Na, Li or Ca as a processing
7 ~~solution (15).~~ solution.

1 10. (currently amended) The nitride semiconductor crystal
2 according to claim 9, wherein

3 said processing solution ~~[(15)]~~ is a liquid
4 containing at least Na and has an Na content of 5-95 mol%.

1 11. (currently amended) The nitride semiconductor crystal
2 according to claim 9, wherein

3 said processing solution ~~[(15)]~~ is a liquid
4 containing at least Li and has an Li content of 5-100 mol%.

1 12. (currently amended) The nitride semiconductor crystal
2 according to claim 9, wherein

3 said nitride semiconductor crystal ~~[(11)]~~ is an
4 $\text{Al}_x\text{Ga}_y\text{In}_{1-x-y}\text{N}$ semiconductor crystal ($0 \leq x \leq 1$, $0 \leq y \leq 1$,
5 $0 \leq x + y \leq 1$).

[AMENDMENT CONTINUES ON NEXT PAGE]